

IN THE CLAIMS

Presented below are the amended claims in a clean, unmarked format:

1. (Three Times Amended) A method of forming a transistor, comprising:
- forming an alignment component on a substrate of a semiconductor material, said alignment component consisting of a single material;
  - depositing a metal layer over the substrate and the alignment component;
  - reacting the metal layer with the semiconductor material of the substrate to form two silicide regions, the silicide regions having inner surfaces which face one another, wherein an upper portion of each inner surface contacts the alignment component and a lower portion of each inner surface contacts the semiconductor material of the substrate;
  - removing the alignment component; and
  - replacing the removed alignment component with a conductive gate.

10. (Twice Amended) The method of claim 1 wherein removing the alignment component includes:
- depositing a layer over the silicide regions and the alignment component;
  - planarizing the layer at least until the alignment component is exposed; and
  - etching the alignment component at least until the substrate is exposed to leave an opening between the inner surfaces of the silicide regions to allow for formation of the gate.